



About = Input Box

TERMS OF USE

Step 1: Operating Specifications

Input Voltage – Min, $V_{IN(min)}$	40 V
Input Voltage – Nom, $V_{IN(nom)}$	48 V
Input Voltage – Max, $V_{IN(max)}$	60 V
Output Voltage, V_{OUT}	12 V
Maximum Output Current, I_{OUT}	8 A
Free-running Switching Frequency, F_{SW}	540 kHz
SYNC Frequency (if used), $F_{SW-SYNC}$	540 kHz
Frequency Set Resistor, R_{CT}	18.7 k Ω

Step 2: Filter Inductor

Recommended Filter Inductance	6.3 μ H
Inductance, L_F	4.7 μ H
Inductor DCR	15 m Ω
PK-to-PK Ripple Current at $V_{IN(nom)}$, ΔI_L	3.6 A pk-pk
Inductor Ripple Current as a % of Max I_{OUT}	45 %

Step 3: $R_{DS(on)}$ or Shunt-Based Current Limit

Shunt, R_S	4.4 m Ω
Required Current Limit Setpoint	8 A
Current Limit Set Resistor, R_{LIM}	274 Ω
Min Inductor Sat Current, $I_{L(SAT)}$	12.0 A
Power Loss in R_S at Full Load, Max V_{IN}	0.18 W

Step 4: Output Capacitance

Output Voltage Ripple Specification	100 mV _{pk-pk}
Minimum Ideal Output Capacitance	8 μ F
Total Output Capacitance (Derated), C_{OUT}	100 μ F
Maximum Permitted ESR	28 m Ω
Output Capacitor ESR	5 m Ω
Resulting Output Voltage Ripple	20 mV _{pk-pk}
Output Capacitor Ripple Current	1.0 A (rms)

Step 5: Input Capacitance

Input Voltage Ripple Specification	500 mV _{pk-pk}
Minimum Ideal Input Capacitance	6 μ F
Total Input Capacitance (Derated), C_{IN}	10 μ F
Maximum Permitted ESR	22 m Ω
Input Capacitor ESR	3 m Ω
Resulting Input Voltage Ripple	310 mV _{pk-pk}
Input Capacitor Ripple Current	3.5 A (rms)

Step 6: Soft-start, UVLO

Soft-Start Time, t_{SS}	4 ms
Soft-Start Capacitance, C_{SS}	47 nF
Input Voltage UVLO Turn-On	14 V
Input Voltage UVLO Turn-Off	13 V
UVLO Upper Resistor, R_{UV1}	100 k Ω
UVLO Lower Resistor, R_{UV2}	9.31 k Ω

If the SYNC feature is not required, connect SYNCIN to GND or VCC for DCM or CCM operation, respectively

Step 7: Compensation Design

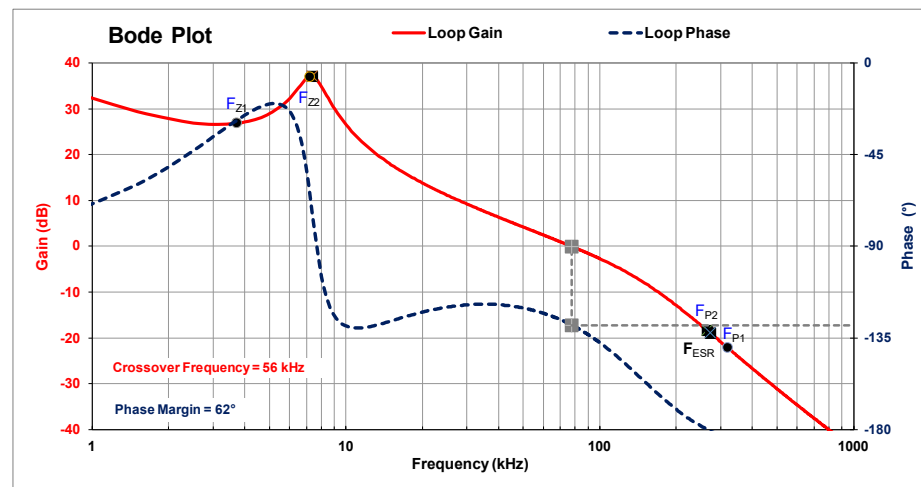
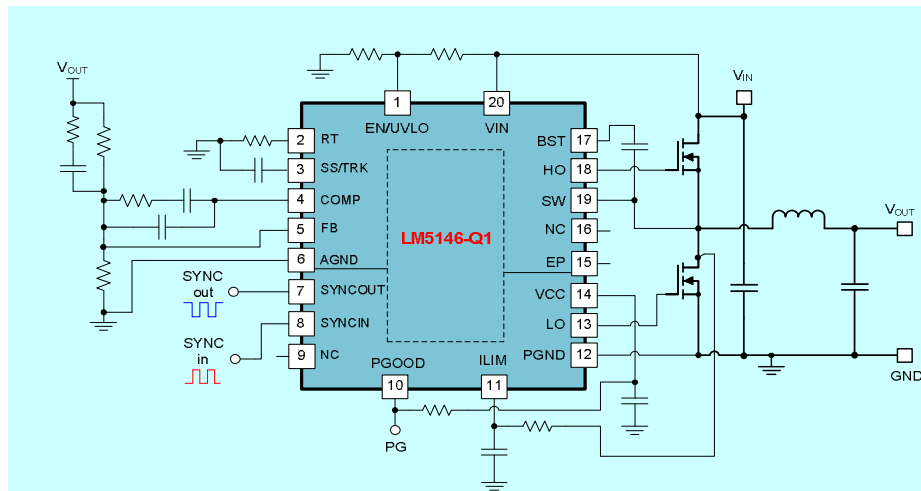
LC Complex Pole Frequency	7.4 kHz
ESR Zero Frequency	318 kHz
Desired Crossover Frequency	63 kHz
Appropriate Midband Gain	0.57 V/V
Upper Feedback Resistor, R_{FB1}	18 k Ω
Lower Feedback Resistor, R_{FB2}	1.3 k Ω
Actual Output Voltage, V_{OUT}	11.877 V

Pole & Zero Placement	
F_{Z1}	5.2 kHz
F_{Z2}	6.6 kHz
F_{P1}	318 kHz
F_{P2}	270 kHz

Baseline P/Z Frequencies:

Compensation Components

	Calculated / Std Values	Selected	Actual P/Z Frequencies
R_{C1}	10.3 / 10.2	13 k Ω	3.7 kHz (F_{Z1})
C_{C1}	3007 / 3300	3300 pF	7.2 kHz (F_{Z2})
C_{C2}	59 / 56	47 pF	272 kHz (F_{P1})
R_{C2}	383 / 383	487 Ω	264 kHz (F_{P2})
C_{C3}	1306 / 1200	1200 pF	



** Specify Inductor Core Loss ** 0.4 W



Efficiency / Power Loss Analyzer

Step 8: Efficiency

High-Side MOSFET (Q_1) Specifications CSD19534Q5A	
On-State Resistance, $R_{DS(on)}$	13 m Ω
Total Gate Charge, Q_G	20 nC
Gate-Drain Charge, Q_{GD}	3.2 nC
Gate-Source Charge, Q_{GS}	5.1 nC
Output Capacitance, C_{OSS}	300 pF
Gate Resistance, R_G	1.5 Ω
Transconductance, g_{fs}	47 S
Gate-Source Threshold Voltage, $V_{GS(th)}$	2.8 V
Body Diode Forward Voltage, V_{SD1}	0.9 V
Thermal Resistance, θ_{JA}	50 $^{\circ}$ C/W

Low-Side MOSFET (Q_2) Specifications BSC037N08NS5	
On-State Resistance, $R_{DS(on)}$	4.4 m Ω
Total Gate Charge, Q_G	50 nC
Output Charge, Q_{OSS}	65 nC
Output Capacitance, C_{OSS}	600 pF
Body Diode Forward Voltage, V_{SD2}	1 V
Body Diode Recovery Charge, Q_{RR}	55 nC
Thermal Resistance, θ_{JA}	50 $^{\circ}$ C/W

Antiparallel Schottky Diode (if applicable)	
Schottky Diode Forward Voltage, V_{SD}	0 V
Schottky Diode Recovery Charge, Q_{RR2}	0 nC

